

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph beginning at page 9, line 18 as follows:

Thus, the photo mask for patterning a lightning rod in accordance with a first preferred embodiment provides a redundancy fine pattern 7 so that the static electricity generated on an array side of the photo mask establishes an equipotential with an adjacent pad through the redundancy fine pattern 7 and is discharged to an outer periphery of the mask even if the fine pattern 6 formed between the lightning rods is broken. Accordingly, even if the fine pattern 6 formed between the lightning rods is short circuited, the photo mask can be protected from static electricity, thereby preventing the photo mask from suffering from damage.

Please amend the paragraph beginning at page 12, line 13 as follows:

Referring to FIG. 10, different from the first, second, third, fourth, or fifth embodiment, the photo mask for patterning a lightning rod in accordance with a sixth preferred embodiment forms no fine pattern for protecting the photo mask from static electricity. That is, the outer lightning rod pattern and the inner lightning rod pattern are formed, not on the same photo mask, but on different photo masks, i.e., the outer lightning rod pattern 2 is formed on a photo mask for patterning a gate line, and the inner lightning rod pattern 3 is formed on a photo mask for patterning a data line. Thus, as the outer and inner lightning rod patterns are formed on different layers of photo masks, forming no lightning rod on an individual photo mask, the photo mask can be protected from suffering [[from]] damage caused by the static electricity.

Please amend the paragraph beginning at page 13, line 1 as follows:

Referring to FIG. 11, the photo mask for patterning a lightning rod in accordance with a

seventh preferred embodiment forms [[of]] the lightning rods by using the related art photo mask for patterning a lightning rod, formation of a contact hole pattern on a following photo mask corresponding to a position of the lightning pattern photo mask where the fine pattern 6 is formed, and the fine pattern 6 part is removed by using the photo mask having the contact hole pattern formed thereon. For an example, if the lightning rod pattern is formed on a photo mask for patterning a gate line, the contact hole pattern is formed on a photo mask for patterning a pixel electrode to be used in a subsequent process at a part of the fine pattern, and any possible fine pattern formed due to defective development and etching during formation of the lightning rod is removed during patterning the pixel electrode.

Please amend the paragraph beginning at page 13, line 17 as follows:

Second, the formation of the fine pattern in a “—“ right angled backward-S form in the second embodiment can reduce short circuits between pads significantly, because bent parts of the “—“ right angled backward-S form are not formed on the substrate, to produce a discontinuity, even if straight parts of the “—“ right angled backward-S form are formed, as interference and diffraction of lights are greater at the bent parts than the straight parts in exposure and development.

Please amend the paragraph beginning at page 14, line 6 as follows:

Sixth, the formation of the outer lightning rod pattern and the inner lightning rod pattern on different photo masks, avoiding formation of the lightning rods on the same photo mask, in the sixth embodiment can prevent the photo mask from suffering damage caused by static electricity.